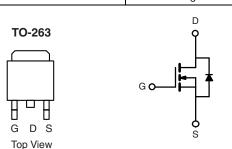


Vishay Siliconix

# Automotive N-Channel 20 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	20				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0013				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0017				
I <sub>D</sub> (A)	120				
Configuration	Single				



N-Channel MOSFET

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R<sub>a</sub> and UIS Tested
- AEC-Q101 Qualifiedd
- Compliant to RoHS Directive 2002/95/EC



FREE

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM120N02-1m3L-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		$V_{DS}$	20	V	
Gate-Source Voltage	$V_{GS}$	± 20	V		
Continuous Drain Currenta	T <sub>C</sub> = 25 °C	1	120		
Continuous Drain Current	T <sub>C</sub> = 125 °C	l <sub>D</sub>	120		
Continuous Source Current (Diode Conduct	I <sub>S</sub>	120	А		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	480			
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	55		
Single Pulse Avalanche Energy	L = 0.1 mm	E <sub>AS</sub>	150	mJ	
Mayimum Dawar Disainationh	T <sub>C</sub> = 25 °C	D	375	W	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	125	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient F	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-Case (Drain)		R <sub>thJC</sub>	0.4	C/VV		

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



# Vishay Siliconix

<b>SPECIFICATIONS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V	-	-	1	T	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V, T <sub>J</sub> = 125 °C	-	-	150	μA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V, T <sub>J</sub> = 175 °C	-	-	500	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 40 A	-	0.0011	0.0013	Ω	
Drain Course On State Resistance		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 40 A, T <sub>J</sub> = 125 °C	-	-	0.0020		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 40 A, T <sub>J</sub> = 175 °C	-	-	0.0023		
		V <sub>GS</sub> = 4.5 V I <sub>D</sub> = 35 A		-	0.0013	0.0017		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 40 A		-	252	-	S	
Dynamic <sup>b</sup>	·							
Input Capacitance	C <sub>iss</sub>			-	11 538	14 500	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 10 V, f = 1 MHz	-	3598	4500		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	1385	1750		
Total Gate Charge <sup>c</sup>	Qg			-	192	290		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 10 \text{ V}, I_{D} = 120 \text{ A}$	-	27	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>				31	-	1	
Gate Resistance	R <sub>g</sub>		f = 1 MHz		1.1	1.8	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD}$ = 10 V, $R_L$ = 0.084 $\Omega$ $I_D \cong$ 120 A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		-	18	27	- ns	
Rise Time <sup>c</sup>	t <sub>r</sub>			-	11	17		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	64	96		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	12	18		
Source-Drain Diode Ratings and Characteristics <sup>b</sup>								
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	480	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 40 A, V <sub>GS</sub> = 0 V		-	0.8	1.5	V	

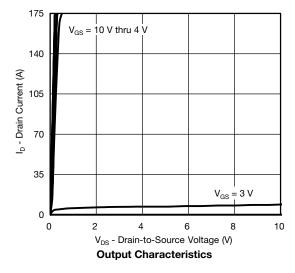
#### Notes

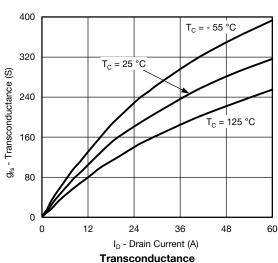
- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

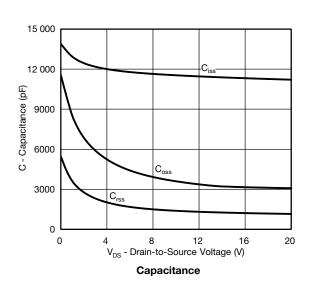
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

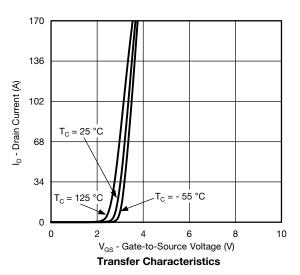


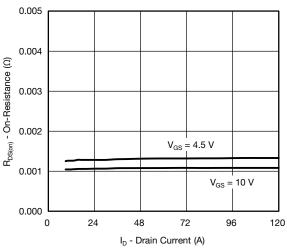
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



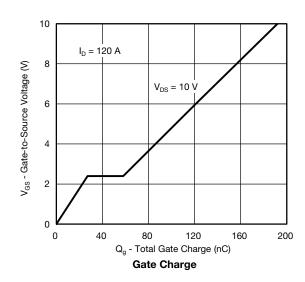






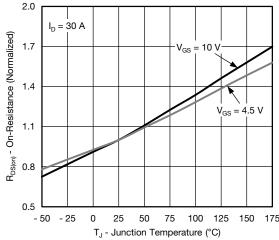


#### On-Resistance vs. Drain Current





## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### On-Resistance vs. Junction Temperature

0.010

0.008

0.006

0.004

0.002

0.000

0

R<sub>DS(on)</sub> - On-Resistance (Ω)



 $T_J = 150 \, ^{\circ}C$ 

8

10

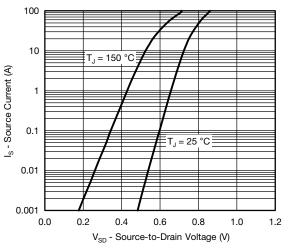
On-Resistance vs. Gate-to-Source Voltage

V<sub>GS</sub> - Gate-to-Source Voltage (V)

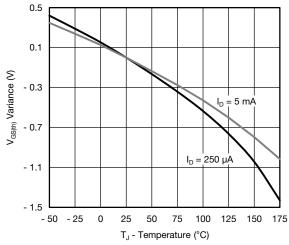
6

 $T_J = 25 \, ^{\circ}C$ 

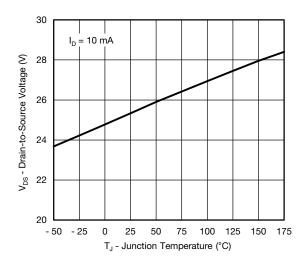
2



**Source Drain Diode Forward Voltage** 



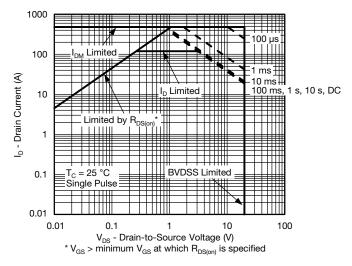
Threshold Voltage



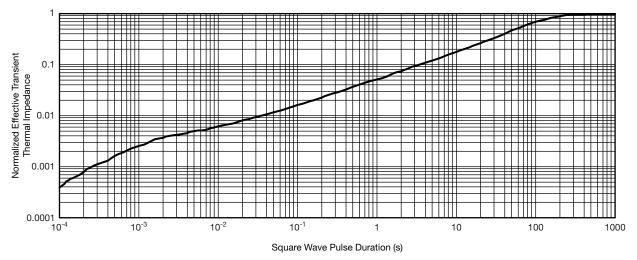
**Drain Source Breakdown vs. Junction Temperature** 



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



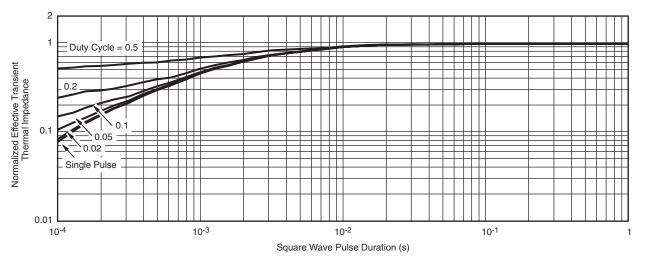
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

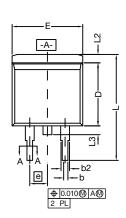
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

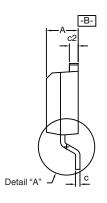
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

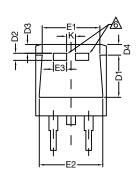
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg263319">www.vishay.com/ppg263319</a>.



# TO-263 (D<sup>2</sup>PAK): 3-LEAD

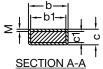








DETAIL A (ROTATED 90°)



_	,	l	o—		ļ	ļ
2:	П			C-1	_	ပ
,	SE	CTI	ON	Δ-4	Δ	Ť

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

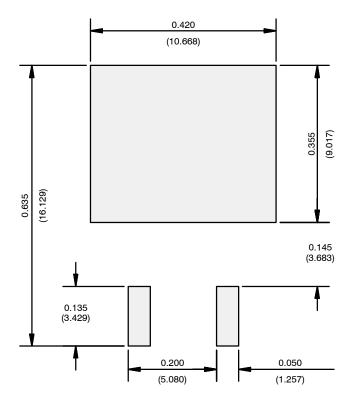
		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	=	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	) BSC	2.54	BSC	
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





## RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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